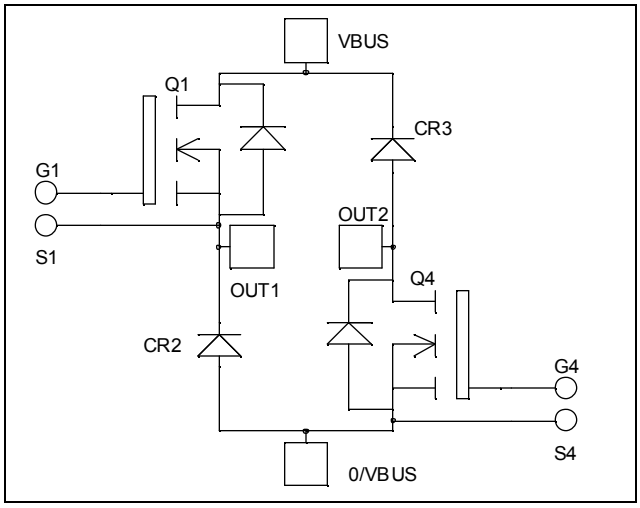
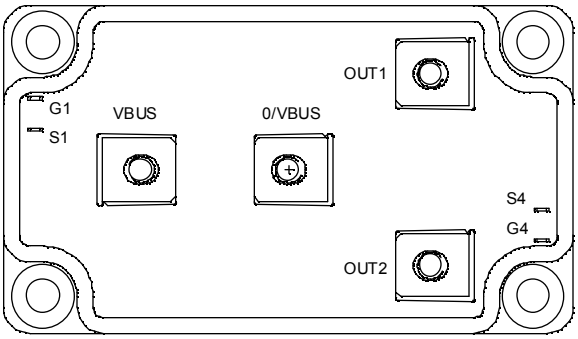
Asymmetrical - bridge MOSFET Power Module

V_{DSS} = 200V
R_{DSon} = 8mΩ typ @ Tj = 25°C
I_D = 208A @ Tc = 25°C





Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 7® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		200	V
I_D	Continuous Drain Current	T_c = 25°C	208	A
		T_c = 80°C	155	
I_{DM}	Pulsed Drain current		832	
V_{GS}	Gate - Source Voltage		±30	V
R_{DSon}	Drain - Source ON Resistance		10	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	781	W
I_{AR}	Avalanche current (repetitive and non repetitive)		100	A
E_{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 200V	T_j = 25°C			375	µA
		V_{GS} = 0V, V_{DS} = 160V	T_j = 125°C			1500	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 104A			8	10	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 5mA		3		5	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±30 V, V_{DS} = 0V				±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		14.4		nF
C_{oss}	Output Capacitance			4.66		
C_{rss}	Reverse Transfer Capacitance			0.29		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 100V I_D = 208A		280		nC
Q_{gs}	Gate – Source Charge			106		
Q_{gd}	Gate – Drain Charge			134		
$T_{d(on)}$	Turn-on Delay Time	**Inductive switching @ 125°C** V_{GS} = 15V V_{Bus} = 133V I_D = 208A R_G = 2.5Ω		32		ns
T_r	Rise Time			64		
$T_{d(off)}$	Turn-off Delay Time			88		
T_f	Fall Time			116		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 133V I_D = 208A, R_G = 2.5Ω		1698		µJ
E_{off}	Turn-off Switching Energy			1858		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 133V I_D = 208A, R_G = 2.5Ω		1872		µJ
E_{off}	Turn-off Switching Energy			1972		

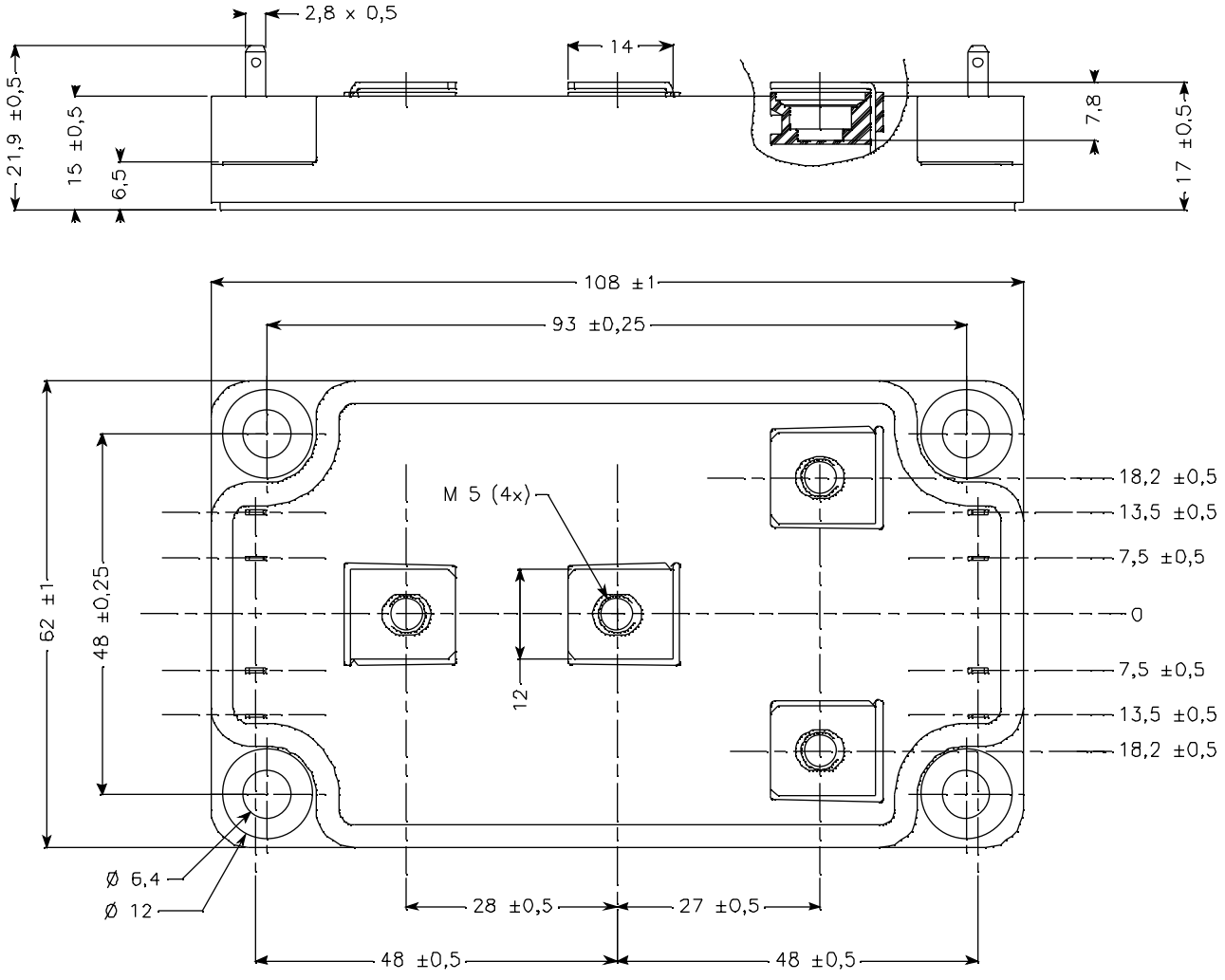
Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=200V	T_j = 25°C			250	µA
			T_j = 125°C			600	
I_F	DC Forward Current		T_c = 75°C		200		A
V_F	Diode Forward Voltage	I_F = 200A			1	1.1	V
		I_F = 400A			1.4		
		I_F = 200A	T_j = 125°C		0.9		
t_{rr}	Reverse Recovery Time	I_F = 200A V_R = 133V di/dt = 400A/µs	T_j = 25°C		60		ns
			T_j = 125°C		110		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		400		nC
			T_j = 125°C		1680		

Thermal and package characteristics

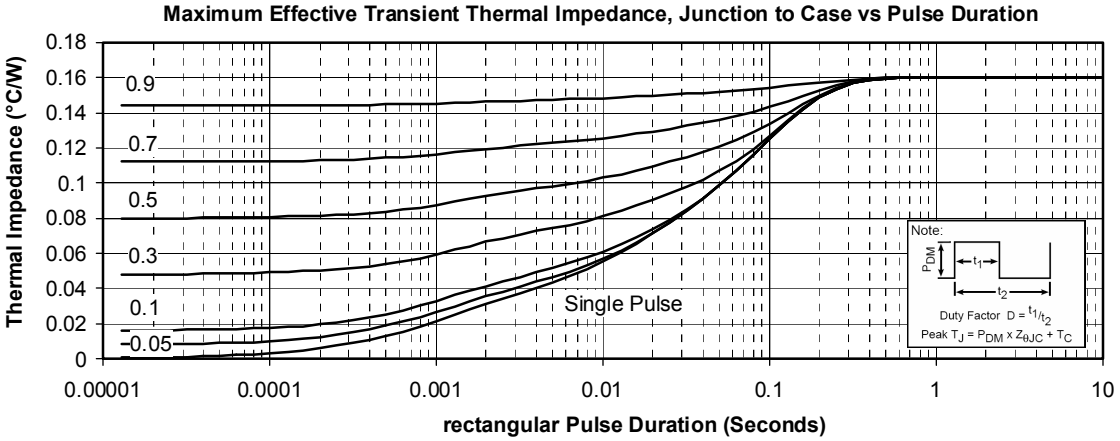
Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance		Transistor			0.16	°C/W
			Diode			0.29	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

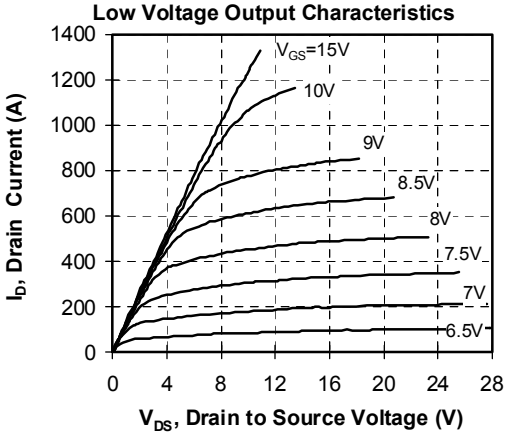
SP6 Package outline (dimensions in mm)

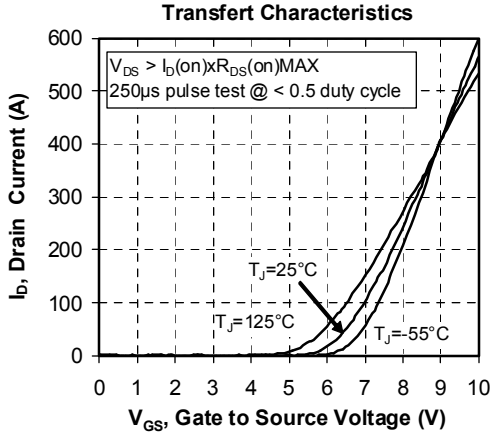


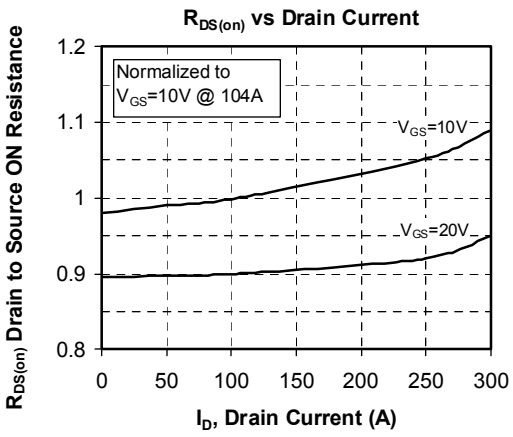
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

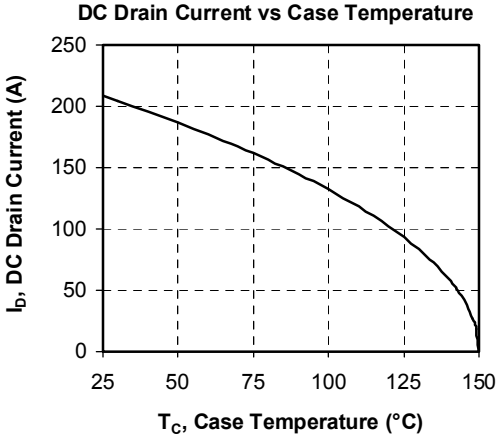
Typical Performance Curve



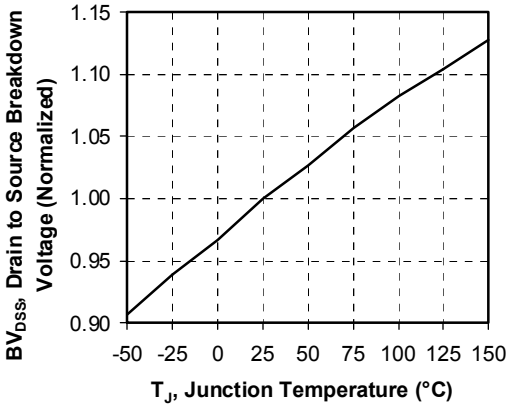




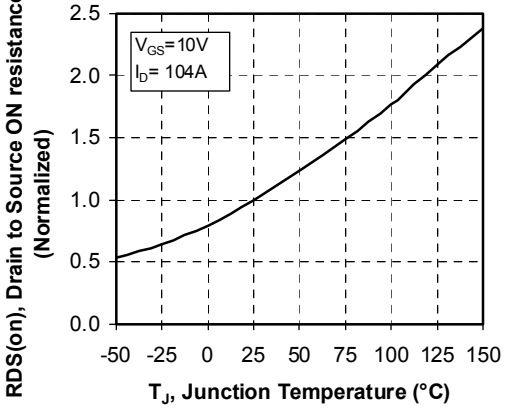




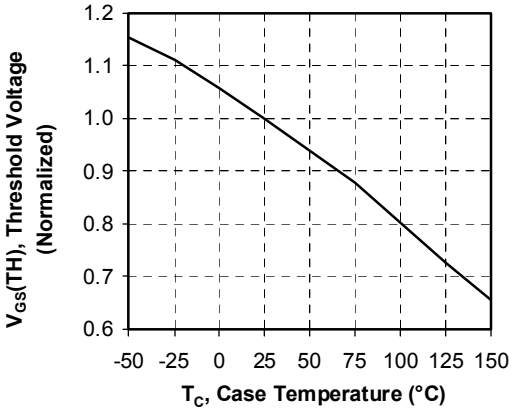
Breakdown Voltage vs Temperature



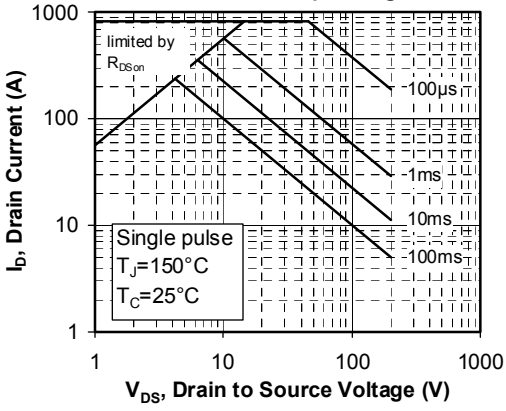
ON resistance vs Temperature



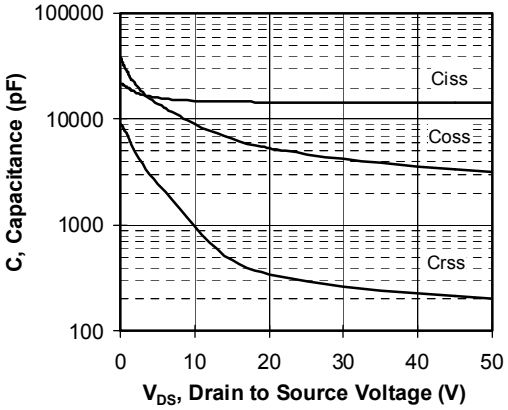
Threshold Voltage vs Temperature



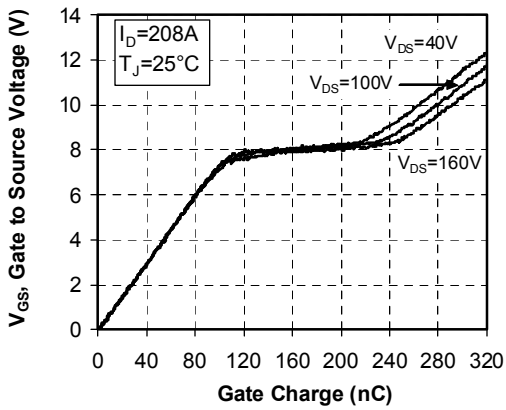
Maximum Safe Operating Area



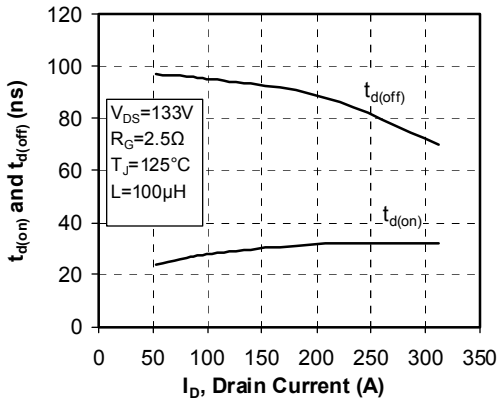
Capacitance vs Drain to Source Voltage



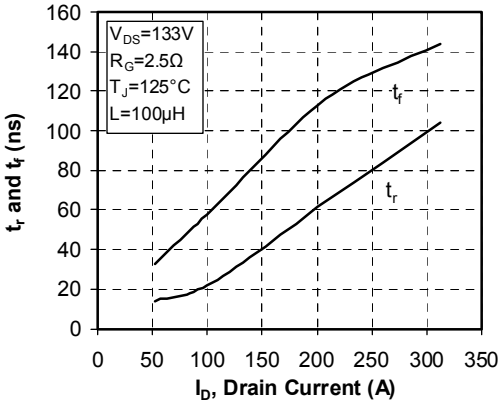
Gate Charge vs Gate to Source Voltage



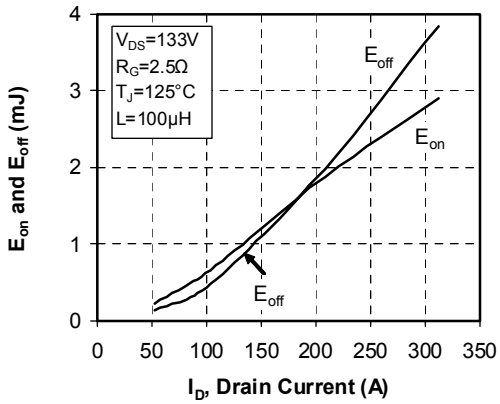
Delay Times vs Current



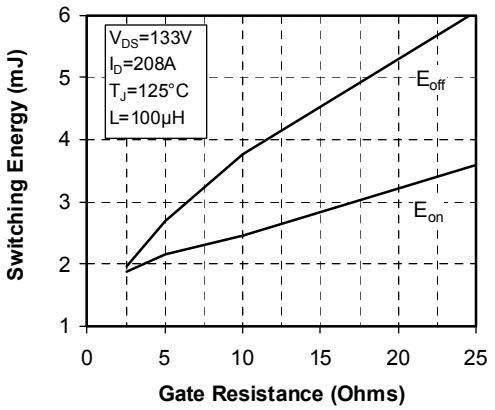
Rise and Fall times vs Current



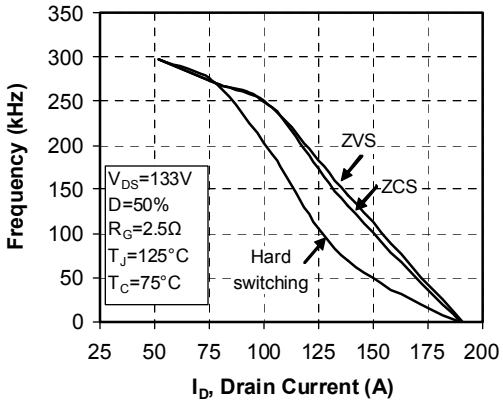
Switching Energy vs Current



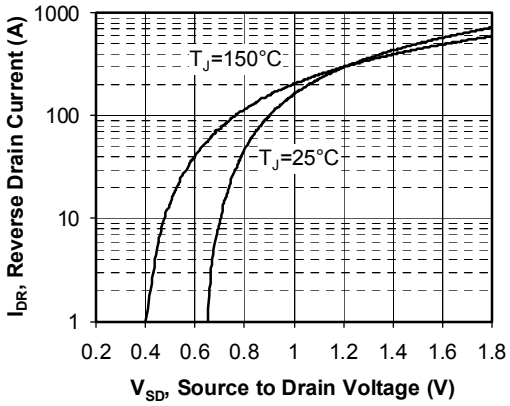
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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